

**General Description**

The UB3010 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The UB3010 meet the RoHS and Green Product requirement with full function reliability approved.

**Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	19	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	12	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	5.4	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	4.3	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	40	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>3</sup>	26	W
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>3</sup>	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

**Thermal Data**

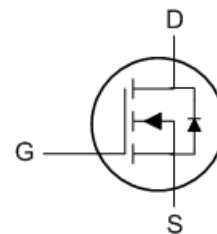
Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	4.8	$^\circ C/W$

**Product Summary**

$BV_{DSS}$	$R_{DS(ON)}$	ID
30V	45m $\Omega$	19A

**Applications**

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

**TO263 Pin Configuration**


**N-Ch 30V Fast Switching MOSFETs**
**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	---	0.016	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=15A$	---	38	45	m $\Omega$
		$V_{GS}=4.5V, I_D=10A$	---	56	70	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-3.04	---	mV/ $^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=15A$	---	3.4	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.3	4.6	$\Omega$
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=15A$	---	2.6	3.64	nC
$Q_{gs}$	Gate-Source Charge		---	1.2	1.68	
$Q_{gd}$	Gate-Drain Charge		---	1.06	1.48	
$T_{d(on)}$	Turn-On Delay Time		---	0.8	1.6	
$T_r$	Rise Time	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=15A$	---	10.8	19.4	ns
$T_{d(off)}$	Turn-Off Delay Time		---	6.4	12.8	
$T_f$	Fall Time		---	4	8.0	
$C_{iss}$	Input Capacitance		---	220	308.0	
$C_{oss}$	Output Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	38	53.2	
$C_{riss}$	Reverse Transfer Capacitance		---	32	44.8	

**Diode Characteristics**

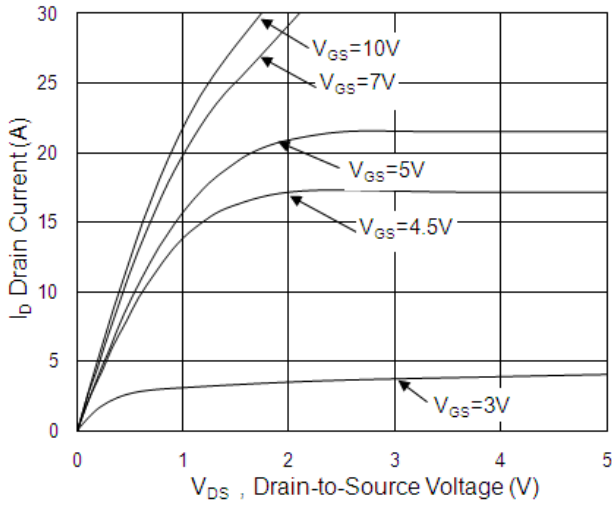
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1, 4</sup>	$V_G=V_D=0V$ , Force Current	---	---	19	A
$I_{SM}$	Pulsed Source Current <sup>2, 4</sup>		---	---	40	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V
$t_{rr}$	Reverse Recovery Time	$I_F=15A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	4.7	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	1.1	---	nC

Note :

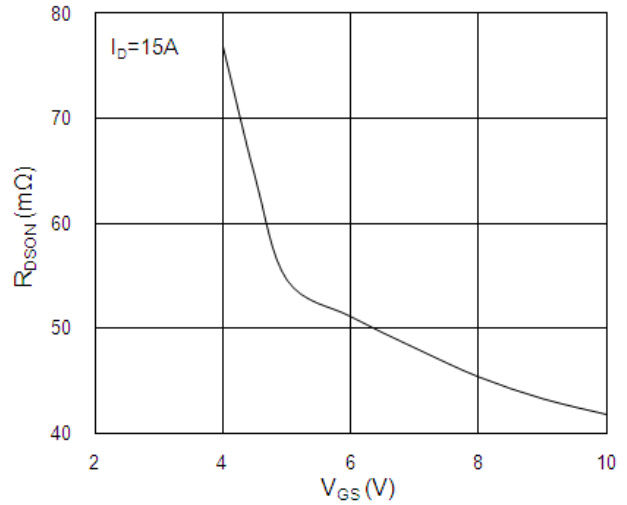
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications , should be limited by total power dissipation.

**N-Ch 30V Fast Switching MOSFETs**

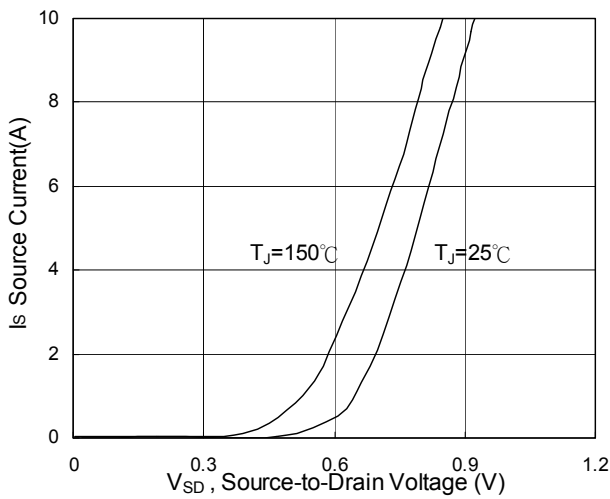
**Typical Characteristics**



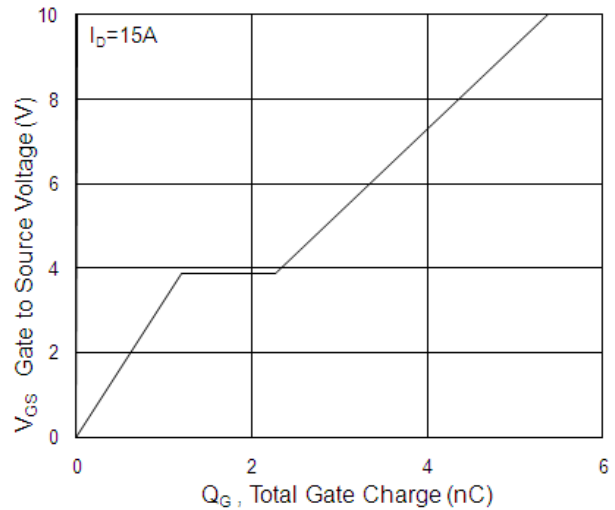
**Fig.1 Typical Output Characteristics**



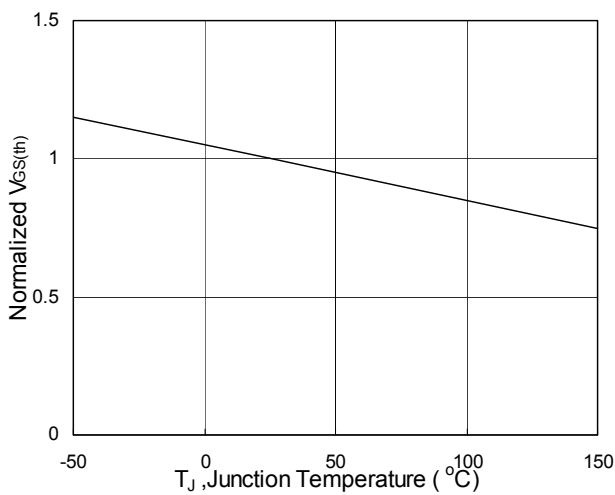
**Fig.2 On-Resistance vs. G-S Voltage**



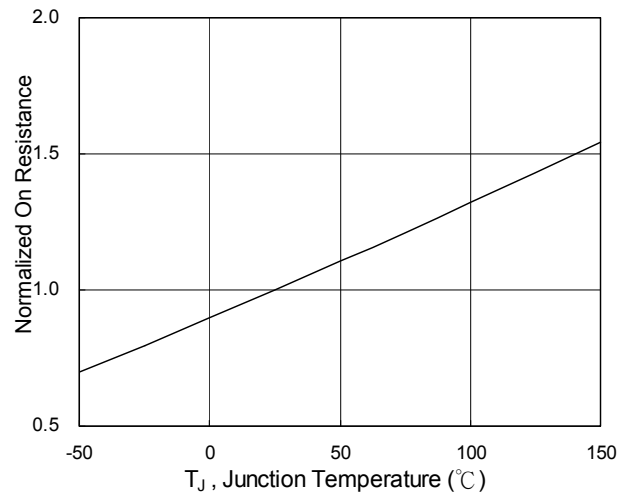
**Fig.3 Forward Characteristics of Reverse**



**Fig.4 Gate-Charge Characteristics**

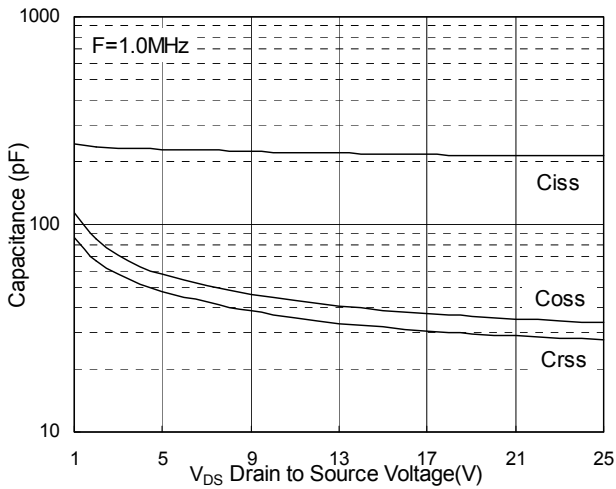


**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**

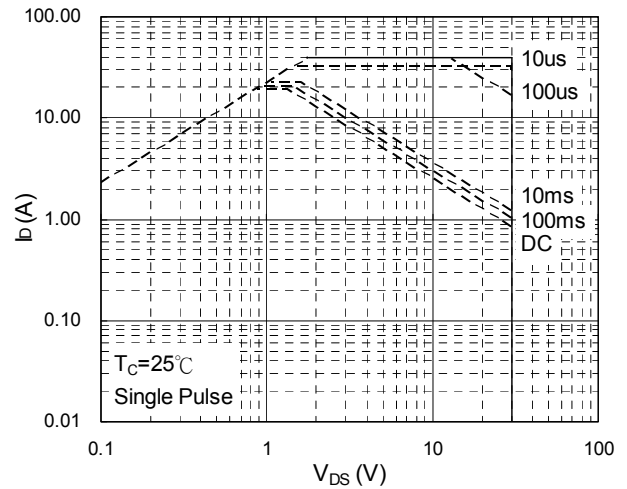


**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**

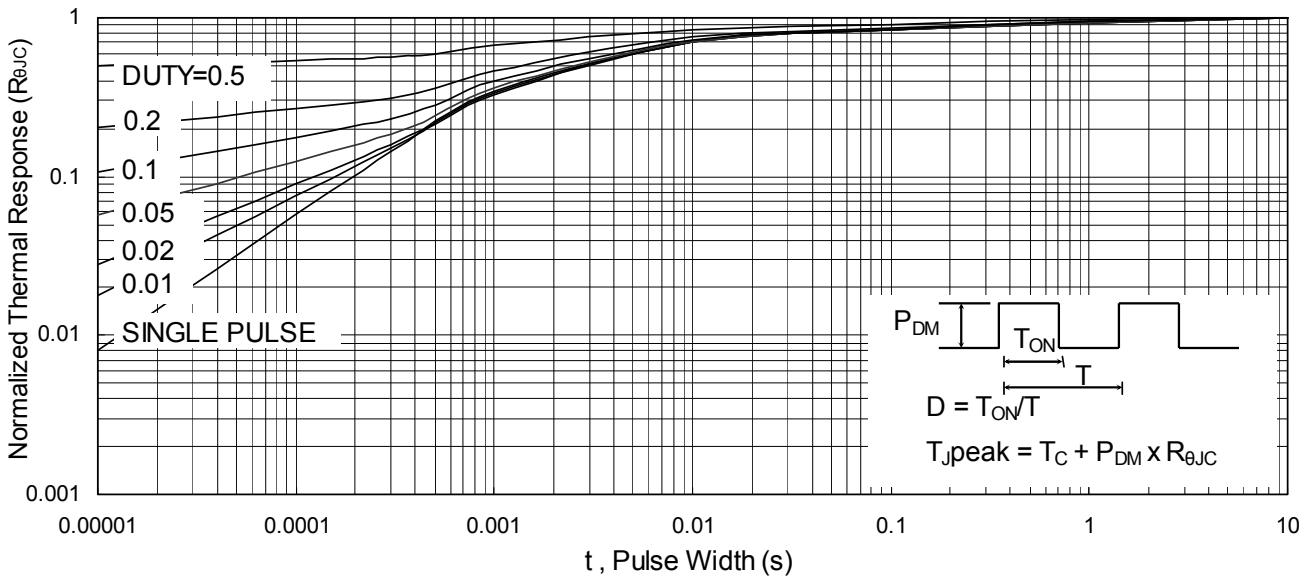
**N-Ch 30V Fast Switching MOSFETs**



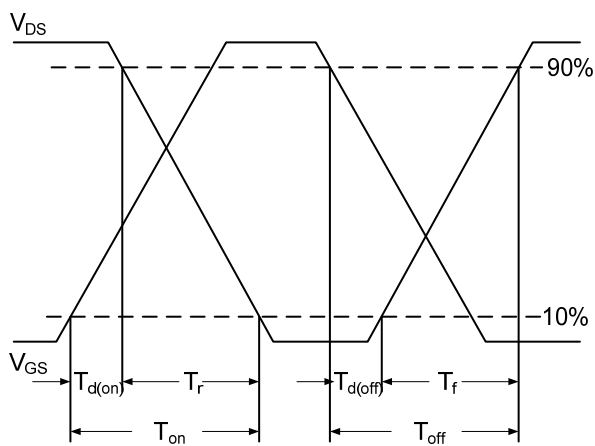
**Fig.7 Capacitance**



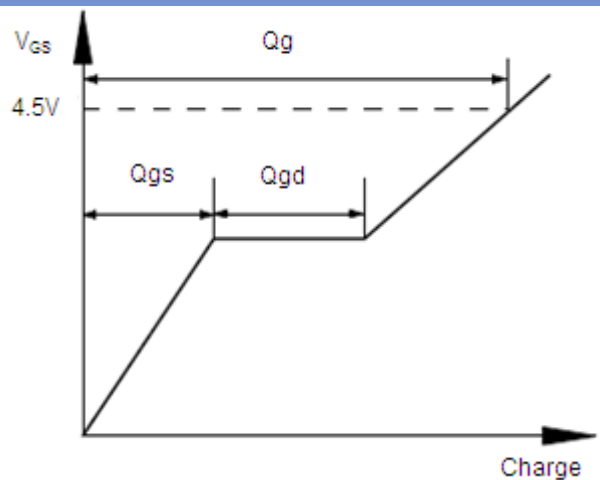
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Gate Charge Waveform**